Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications.

2. Features and benefits

- High blocking voltage capability
- Least sensitive gate for highest noise immunity
- High minimum I_{GT} for guaranteed immunity to gate noise
- Planar passivated for voltage ruggedness and reliability
- · Triggering in all four quadrants

3. Applications

- General purpose motor controls
- Lighting controls
- Applications where only positive gate drive is avaliable
- Applications where gate noise or interference may occur

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	65	A
Tj	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	-	8	A
Static char	acteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	10	-	50	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	10	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	10	-	100	mA
Dynamic char	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	704	G sym051
3	G	gate		·
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BT137-800G0	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 102 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	8	Α

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Symbol	Parameter	Conditions	Min	Max	Unit
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; $\underline{\text{Fig. 4}}$; $\underline{\text{Fig. 5}}$	-	65	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	71	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	21	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G+	-	50	A/µs
		I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2+ G-	-	50	A/µs
		I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G-	-	50	A/µs
		I_T = 12 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

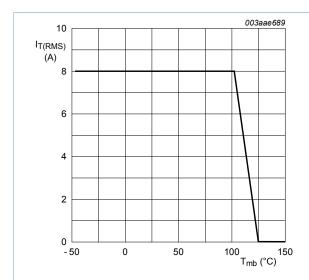
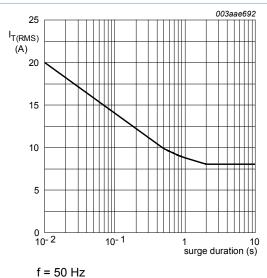


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

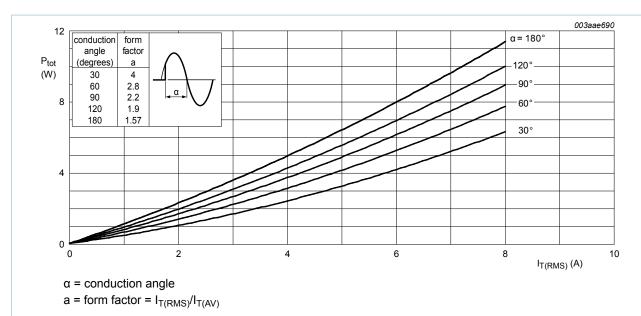


T = 50 Hz $T_{\text{mb}} \le 102 \text{ °C}$

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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Total power dissipation as a function of RMS on-state current; maximum values

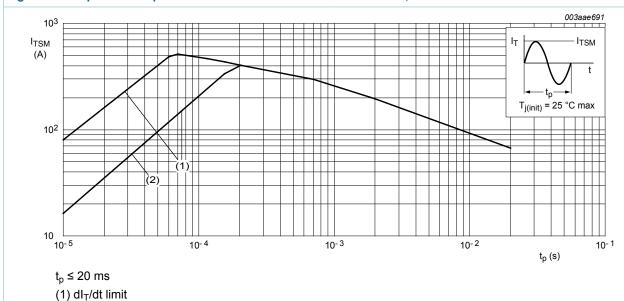
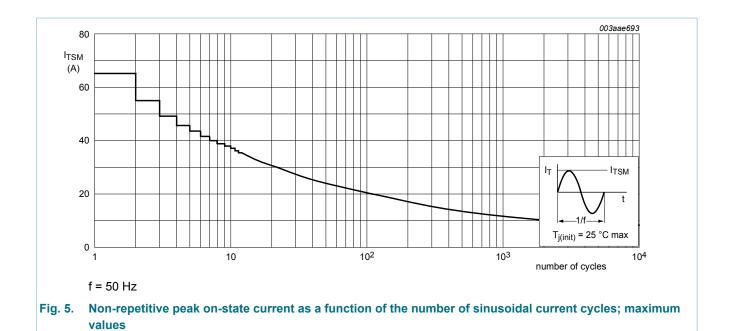


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

(2) T2- G+ quadrant limit

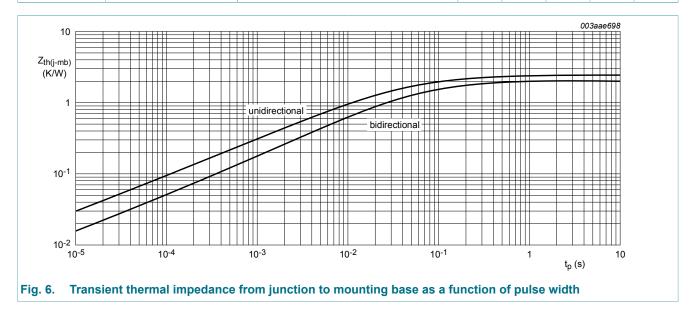
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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig. 6	-	-	2	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



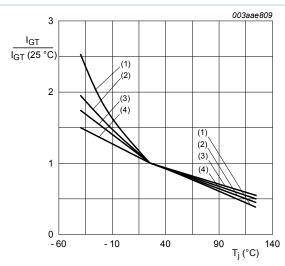
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9. Characteristics

Table 6 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics		<u> </u>			
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	10	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	10	-	100	mA
L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	45	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	-	45	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	-	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	40	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics		'			,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	200	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 95 °C; dI_{com}/dt = 3.6 A/ ms; I_T = 8 A; gate open circuit	10	-	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 12 A; V_D = 800 V; I_G = 0.1 mA; dI_G/dt = 5 A/µs	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

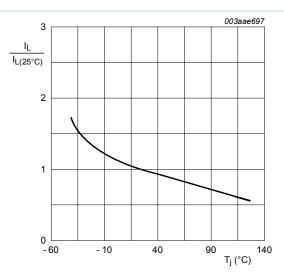


Fig. 8. Normalized latching current as a function of junction temperature

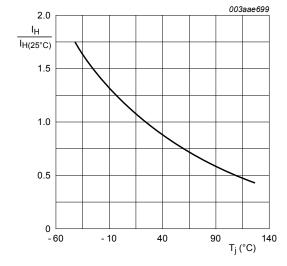
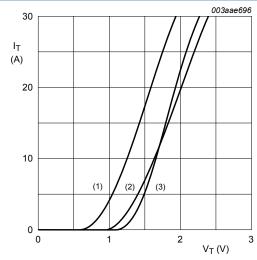


Fig. 9. Normalized holding current as a function of junction temperature



- $V_0 = 1.264 \text{ V}$
- $R_s = 0.038 \Omega$
- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) $T_j = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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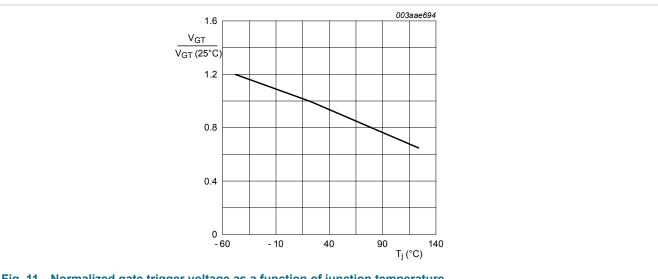
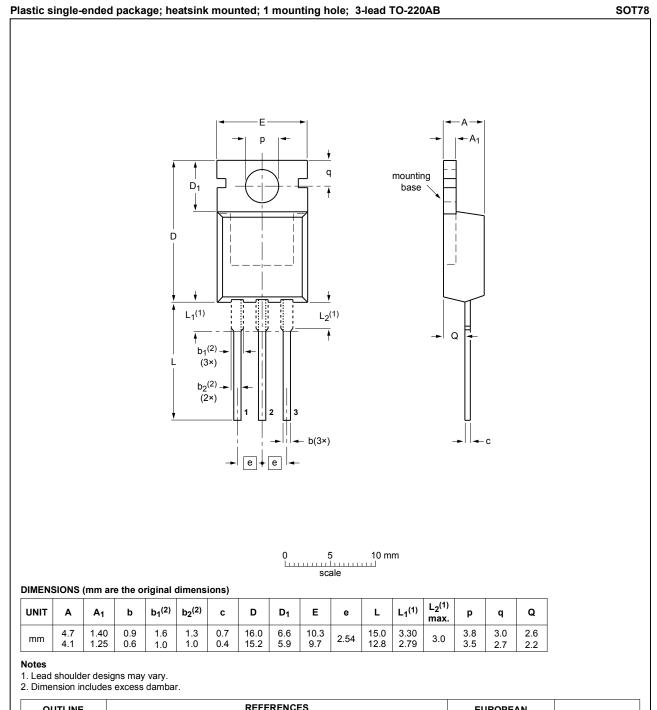


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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10. Package outline



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

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